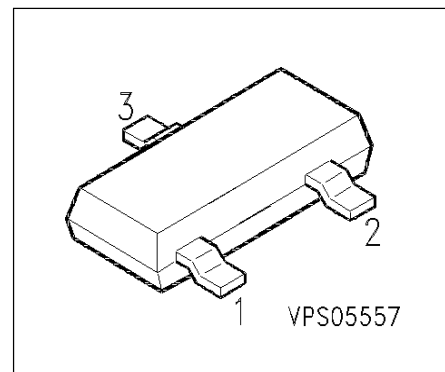**Preliminary Data**

BSS 159

SIPMOS ® Small-Signal Transistor

- N channel

- Depletion mode

- High dynamic resistance

VPS05557

Pin 1	Pin 2	Pin 3
G	S	D

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Marking	Ordering Code
BSS 159	50 V	0.16 A	8 Ω	SOT-23	SEs	Q67000-S321

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain source voltage	V_{DS}	50	V
Drain-gate voltage R_{GS} = 20 kΩ	V_{DGR}	 50	
Gate source voltage	V_{GS}	± 14	
Gate-source peak voltage, aperiodic	V_{gs}	± 20	
Continuous drain current T_A = 25 ˚C	I_D	 0.16	A
DC drain current, pulsed T_A = 25 ˚C	I_{Dpuls}	 0.48	
Power dissipation T_A = 25 ˚C	P_{tot}	 0.36	W
Chip or operating temperature	T_j	-55 ... + 150	˚C
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip to ambient air	R_{thJA}	≤ 350	K/W
Therminal resistance, chip-substrate - reverse side [1]	R_{thJSR}	≤ 285	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

Electrical Characteristics, at $T_j = 25°C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage V_{GS} = -10 V, I_D = 250 µA	$V_{(BR)DSV}$	50	-	-	V
Gate threshold voltage V_{DS} = 3 V, I_D = 10 µA	$V_{GS(th)}$	-3	-2.5	-1.5	
Drain-source cutoff current V_{DS} = 50 V, V_{GS} = -10 V, T_j = 25 °C	I_{DSV}	-	-	1	µA
On-state drain current V_{GS} = 0 V, V_{DS} = 10 V	$I_{D(on)}$	70	200	-	mA
Gate-source leakage current V_{GS} = 20 V, V_{DS} = 0 V	I_{GSS}	-	10	100	nA
Drain-Source on-resistance V_{GS} = 0 V, I_D = 0.07 A	$R_{DS(on)}$	-	4	8	Ω

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max},\ I_D = 0.16$ A	g_{fs}	0.1	0.16	-	S
Input capacitance $V_{GS} = -4.5$ V, $V_{DS} = 25$ V, $f = 1$ MHz	C_{iss}	-	70	100	pF
Output capacitance $V_{GS} = -4.5$ V, $V_{DS} = 25$ V, $f = 1$ MHz	C_{oss}	-	15	25	
Reverse transfer capacitance $V_{GS} = -4.5$ V, $V_{DS} = 25$ V, $f = 1$ MHz	C_{rss}	-	6	9	
Turn-on delay time $V_{DD} = 30$ V, $V_{GS} = -5... + 5$ V, $I_D = 0.28$ A $R_{GS} = 50\ \Omega$	$t_{d(on)}$	-	7	11	ns
Rise time $V_{DD} = 30$ V, $V_{GS} = -5... + 5$ V, $I_D = 0.28$ A $R_{GS} = 50\ \Omega$	t_r	-	11	17	
Turn-off delay time $V_{DD} = 30$ V, $V_{GS} = -5... + 5$ V, $I_D = 0.28$ A $R_{GS} = 50\ \Omega$	$t_{d(off)}$	-	13	17	
Fall time $V_{DD} = 30$ V, $V_{GS} = -5... + 5$ V, $I_D = 0.28$ A $R_{GS} = 50\ \Omega$	t_f	-	14	19	

Electrical Characteristics, at T_j = 25˚C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current T_A = 25 ˚C	I_S	-	-	0.1	A
Inverse diode direct current,pulsed T_A = 25 ˚C	I_{SM}	-	-	0.3	
Inverse diode forward voltage V_{GS} = 0 V, I_F = 0.3 A	V_{SD}	-	0.8	1.3	V